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View Online at https://aerobasegroup.com/nsn/5961-01-053-3316
Inclosure Material:
Ceramic
Overall Length:
Between 0.890 inches and 0.910 inches
Overall Height:
0.240 inches
Overall Width:
Between 0.376 inches and 0.410 inches
End Application:
An/fps-115
Mounting Facility Quantity:
2
Internal Configuration:
Junction contact
Electrode Internally-electrically Connected To Case:
Base
Mounting Method:
Unthreaded hole
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
65.0 collector to base voltage/static/emitter open and 25.0 collector to emitter voltage/static/base open and 4.0 emitter to base voltage,
instantaneous
Current Rating Per Characteristic:
10.00 amperes source cutoff current
Power Rating Per Characteristic:
80.0 watts small-signal input power, common-collector absolute
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction
Special Features:
T.O. 31p6-2fps115-62; n/h/a rf amplifier; junction pattern arrangement: npn
Precious Material And Location:
Plated leads gold
Precious Material:
Gold
Test Data Document:
49956-914509 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
2 ribbon and 1 case
Shelf Life:
N/a

Unit Of Measure:

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No

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